A.G. Ostrogorsky, Professor

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A. Ostrogorsky received his Dipl. Ing. degree in Mechanical Engineering at the University of Belgrade (1977), MS in Nuclear Engineering at R.P.I. (1981), and Sc.D. in Mechanical Engineering at MIT (1986). He was a Post-doctoral associate, in Professor A.F. Witt’s Crystal Growth Laboratory, at MIT, Assistant Professor at Columbia University (1987-1992), and Alexander von Humboldt Fellow in Professor Georg Muller’s Laboratory, at Universität Erlanger-Nürnberg (1991). In 1993 he joined Rensselaer Polytechnic Institute (RPI) as Associate Professor.

Professor Ostrogorsky was Director of the Center for Microgravity and Materials Research (CMMR), and Professor at the University of Alabama in Huntsville (1999-2000). He was Professor at RPI until 2009, when he moved to the Illinois Institute of Technology in Chicago, where he is currently Professor of Materials and Aerospace Engineering.

He was Principal Investigator of the NASA sponsored investigations conducted at the International Space Station (ISS): the SUBSA investigation 1996-2004 and the 2016-present CASIS/NASA project on growing InI crystals for nuclear detector applications.

He is Fellow of ASME, Member of the Executive Committee of AACG, Associated Editor of the Journal of Crystal Growth, Associate Fellow of AIAA.

Selected Publications:

1. N. Dropka and A.G. Ostrogorsky, “Interface control in vertical Bridgman growth by shaped and flat rotating baffles“, J. Crystal Growth 526 (2019)125221
2. A.G. Ostrogorsky and B.B. Mikic, “Semi-Infinite Solid Solution Adjusted for Radial Systems Using Time-Dependent Participating Volume-to-Surface Ratio for Finite Solids“, ASME J. Heat Transfer 140 (2018)101301p1-10
3. A.G. Ostrogorsky, V. Riabova, N. Dropka, “Interface control by rotating submerged heater/baffle in vertical Bridgman T configuration “J. Crystal Growth 498 (2018) 269–276
4. A. Cröll, J. Markert, M. Volz and A.Ostrogorsky, ”Wetting angles of monovalent indium iodide on different substrates”, Cryst. Res. Technol. 52, No. 1, 1600179 (2017) .
5. A.G. Ostrogorsky and M.E. Glicksman, Chapter 25, "Segregation and component distribution” Handbook of Crystal Growth, 2nd ed. T. Nishinaga, T. Kuech and P. Rudolph, Editors (2015) p 995-147
6. A.G. Ostrogorsky, “Empirical Correlations for Natural Convection, Δ and keff,” J. Crystal Growth, Volume 426, 15 September 2015, Pages 38-48
7. A.G. Ostrogorsky, “Effective convection coefficient for porous interface and solute segregation”, J. Crystal Growth 348 (2012) 97–105.
8. I. Nicoara, D.Nicoara, C. Bertorello, G.A. Slack and A. G. Ostrogorsky, M. Groza and A. Burger “Czochralski Growth of Indium Iodide and other Wide Bandgap Semiconductor Compounds”, MRS Proc. 1341 (2011) 95-104.
9. A.G. Ostrogorsky, C. Marin, M. Volz, T. Duffar.,“ [Initial transient in Zn-doped InSb grown in microgravity](http://www.sciencedirect.com/science?_ob=ArticleURL&_udi=B6TJ6-4W0WJCF-1&_user=4558833&_coverDate=06%2F01%2F2009&_alid=1211941965&_rdoc=2&_fmt=high&_orig=search&_cdi=5302&_sort=d&_docanchor=&view=c&_ct=29&_acct=C000047720&_version=1&_urlVersion=0&_userid=4558833&md5=e7406afbfdf3d65b6fb807850b0a0dec)”, J. Crystal Growth 311(2009) 3243-3248
10. A. G. Ostrogorsky, C. Marin, A.Churilov, Martin Volz, W.A. Bonner, T. Duffar, “ Reproducible Te-doped InSb Experiments in Microgravity Science Glovebox at the International Space Station”, *J. Crystal Growth 310*  (2008) 364-371.